

**IR-Lumineszenzdiode (850 nm) mit hoher Ausgangsleistung**  
**High Power Infrared Emitter (850 nm)**  
**Lead (Pb) Free Product - RoHS Compliant**  
**SFH 4232**



**Vorläufige Daten / Preliminary Data**

**Wesentliche Merkmale**

- IR-Lichtquelle mit hohem Wirkungsgrad
- Chipgröße (emittierende Fläche) 1 x 1 mm<sup>2</sup>
- max. Gleichstrom 1 A
- niedriger Wärmewiderstand (9 K/W)
- Schwerpunktwellenlänge 850 nm
- ESD-sicher bis 2 kV nach JESD22-A114-E

**Features**

- IR lightsource with high efficiency
- die-size (emitting area) 1 x 1 mm<sup>2</sup>
- max. DC-current 1 A
- Low thermal resistance (9 K/W)
- Center of spectral emission at 850 nm
- ESD save up to 2 kV acc. to JESD22-A114-E

**Anwendungen**

- Infrarotbeleuchtung für Kameras
- Überwachungssysteme
- Fahrer-Assistenz Systeme
- Beleuchtung für Bilderkennungssysteme

**Applications**

- Infrared illumination for cameras
- Surveillance systems
- Driver assistance systems
- Machine vision systems

**Sicherheitshinweise**

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheitsrichtlinien der IEC-Normen 60825-1 und 62471 behandelt werden.

**Safety Advices**

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Typ Type	Bestellnummer Ordering Code	Gesamtstrahlungsfluss <sup>1)</sup> ( $I_F = 1A, t_p = 10\text{ ms}$ ) Total Radiant Flux <sup>1)</sup> $\Phi_e$ (mW)
SFH 4232	Q65110A8754	$\geq 320$ (typ. 530)

<sup>1)</sup> gemessen mit Ulbrichtkugel / measured with integrating sphere

**Grenzwerte** ( $T_A = 25\text{ °C}$ )**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}, T_{stg}$	- 40 ... + 100	°C
Sperrschichttemperatur Junction temperature	$T_J$	+ 125	°C
Sperrspannung Reverse voltage	$V_R$	1	V
Vorwärtsgleichstrom Forward current	$I_F$	1	A
Stoßstrom, $t_p < 200\ \mu\text{s}$ , $D = 0$ Surge current	$I_{FSM}$	5	A
Leistungsaufnahme Power consumption	$P_{tot}$	1.8	W
Wärmewiderstand Sperrschicht - Lötstelle Thermal resistance junction - soldering point	$R_{thJS}$	9	K/W

**Kennwerte** ( $T_A = 25\text{ °C}$ )**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 1\text{ A}$ , $t_p = 10\text{ ms}$	$\lambda_{peak}$	860	nm
Schwerpunktswellenlänge der Strahlung Centroid wavelength $I_F = 1\text{ A}$ , $t_p = 10\text{ ms}$	$\lambda_{centroid}$	850	nm
Spektrale Bandbreite bei 50% von $I_{max}$ Spectral bandwidth at 50% of $I_{max}$ $I_F = 1\text{ A}$ , $t_p = 10\text{ ms}$	$\Delta\lambda$	30	nm
Abstrahlwinkel Half angle	$\varphi$	$\pm 60$	Grad deg.
Aktive Chipfläche Active chip area	$A$	1	mm <sup>2</sup>
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	1 × 1	mm <sup>2</sup>

**Kennwerte** ( $T_A = 25\text{ °C}$ )  
**Characteristics** (cont'd)

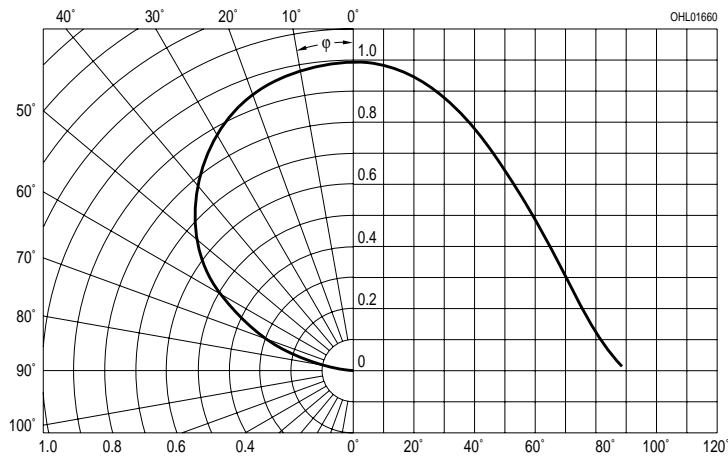
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, $I_e$ von 10% auf 90% und von 90% auf 10%, $I_F = 5\text{ A}$ , $R_L = 50\ \Omega$ Switching times, $I_e$ from 10% to 90% and from 90% to 10%, $I_F = 5\text{ A}$ , $R_L = 50\ \Omega$	$t_r / t_f$	7 / 14	ns
Durchlassspannung Forward voltage $I_F = 1\text{ A}$ , $t_p = 100\ \mu\text{s}$ $I_F = 5\text{ A}$ , $t_p = 100\ \mu\text{s}$	$V_F$ $V_F$	1.5 (< 1.8) 2.0 (< 2.9)	V V
Strahlstärke Radiant intensity $I_F = 1\text{ A}$ , $t_p = 100\ \mu\text{s}$	$I_{e\text{ typ}}$	180	mW/sr
Temperaturkoeffizient von $I_e$ bzw. $\Phi_e$ Temperature coefficient of $I_e$ or $\Phi_e$ $I_F = 1\text{ A}$ , $t_p = 10\text{ ms}$	$TC_I$	- 0.3	%/K
Temperaturkoeffizient von $V_F$ Temperature coefficient of $V_F$ $I_F = 1\text{ A}$ , $t_p = 10\text{ ms}$	$TC_V$	- 1	mV/K
Temperaturkoeffizient von $\lambda$ Temperature coefficient of $\lambda$ $I_F = 1\text{ A}$ , $t_p = 10\text{ ms}$	$TC_{\lambda,\text{centroid}}$	+ 0.3	nm/K

**Gesamtstrahlungsfluss<sup>1)</sup>  $\Phi_e$**   
**Total Radiant Flux<sup>1)</sup>  $\Phi_e$**

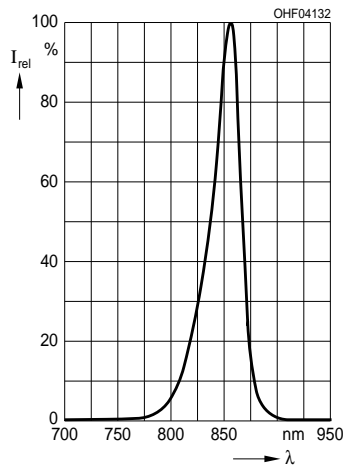
Bezeichnung Parameter	Symbol	Werte Values			Einheit Unit
		-CB	-DA	-DB	
Gesamtstrahlungsfluss Total Radiant Flux $I_F = 1 \text{ A}, t_p = 10 \text{ ms}$	$\Phi_{e \text{ min}}$ $\Phi_{e \text{ max}}$	320 500	400 630	500 800	mW mW

<sup>1)</sup> Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 1.6:1) /  
 Only one group in one packing unit (variation lower 1.6:1)

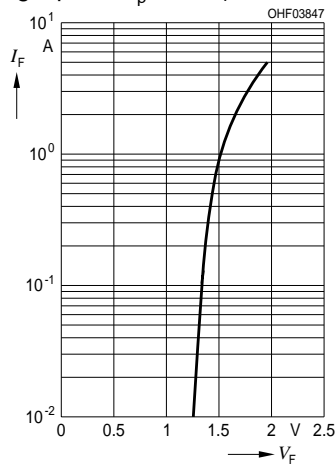
**Abstrahlcharakteristik**  
**Radiation Characteristics  $I_{\text{rel}} = f(\varphi)$**



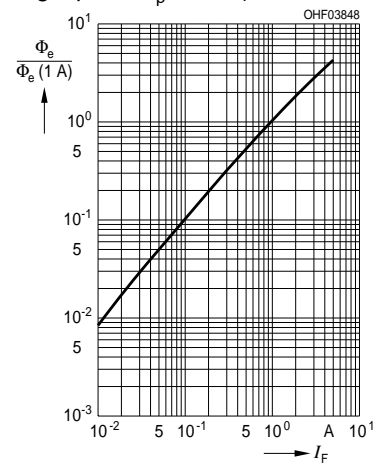
**Relative spektrale Emission**  
**Relative Spectral Emission**  
 $I_{rel} = f(\lambda)$



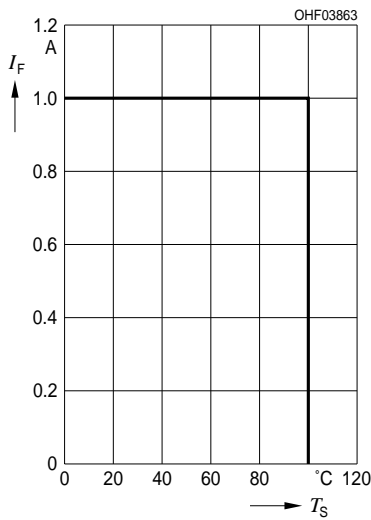
**Durchlassstrom**  
**Forward Current**  
 $I_F = f(V_F)$   
 Single pulse,  $t_p = 100 \mu s$



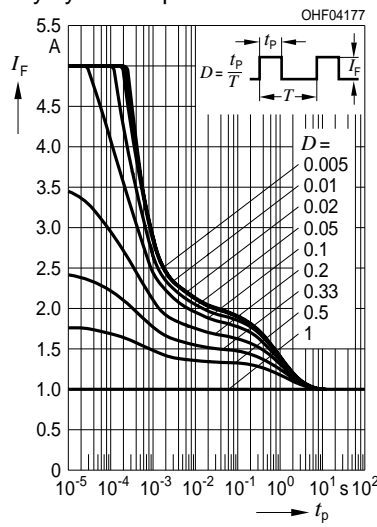
**Relativer Gesamtstrahlungsfluss**  
**Relative Total Radiant Flux**  
 $\Phi_e / \Phi_e(1000mA) = f(I_F)$   
 Single pulse,  $t_p = 100 \mu s$



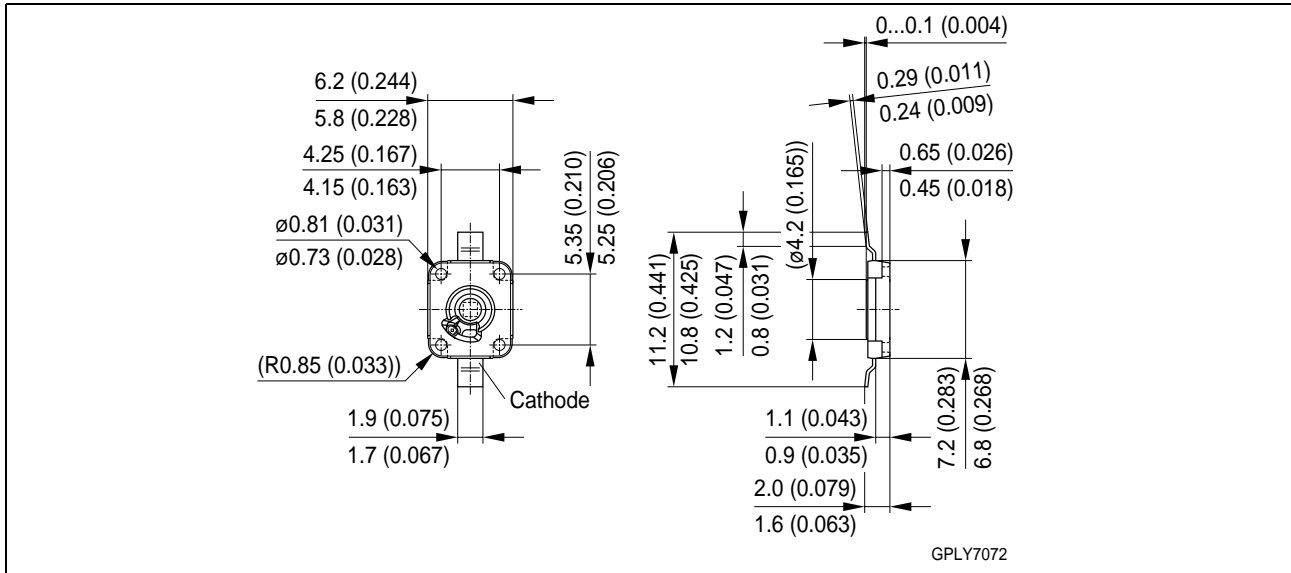
**Max. zulässiger Durchlassstrom**  
**Max. Permissible Forward Current**  
 $I_F = f(T_A), R_{thJS} = 9 K/W$



**Zulässige Impulsbelastbarkeit**  
**Permissible Pulse Handling Capability**  
 $I_F = f(t_p), T_S = 85^\circ C$ ,  
 Duty cycle  $D = \text{parameter}$



**Maßzeichnung<sup>1)</sup>**  
**Package Outlines**



**Kathodenkennung:**

**Cathode mark:**

**Gewicht / Approx. weight:**

**Markierung**

**mark**

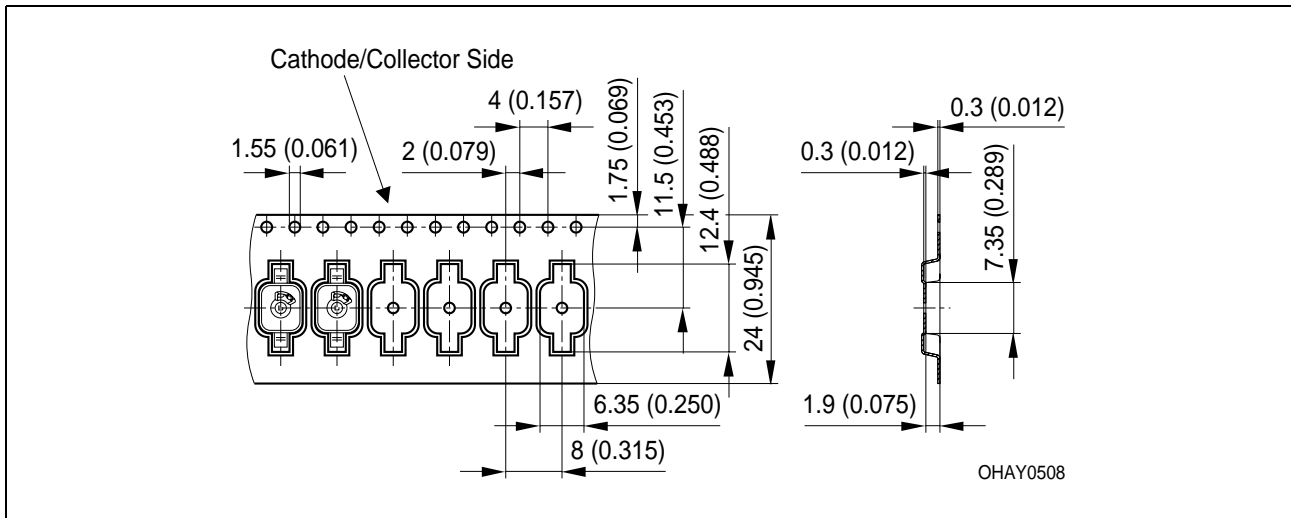
**0.2 g**

**Gurtung / Polarität und Lage**

**Method of Taping / Polarity and Orientation**

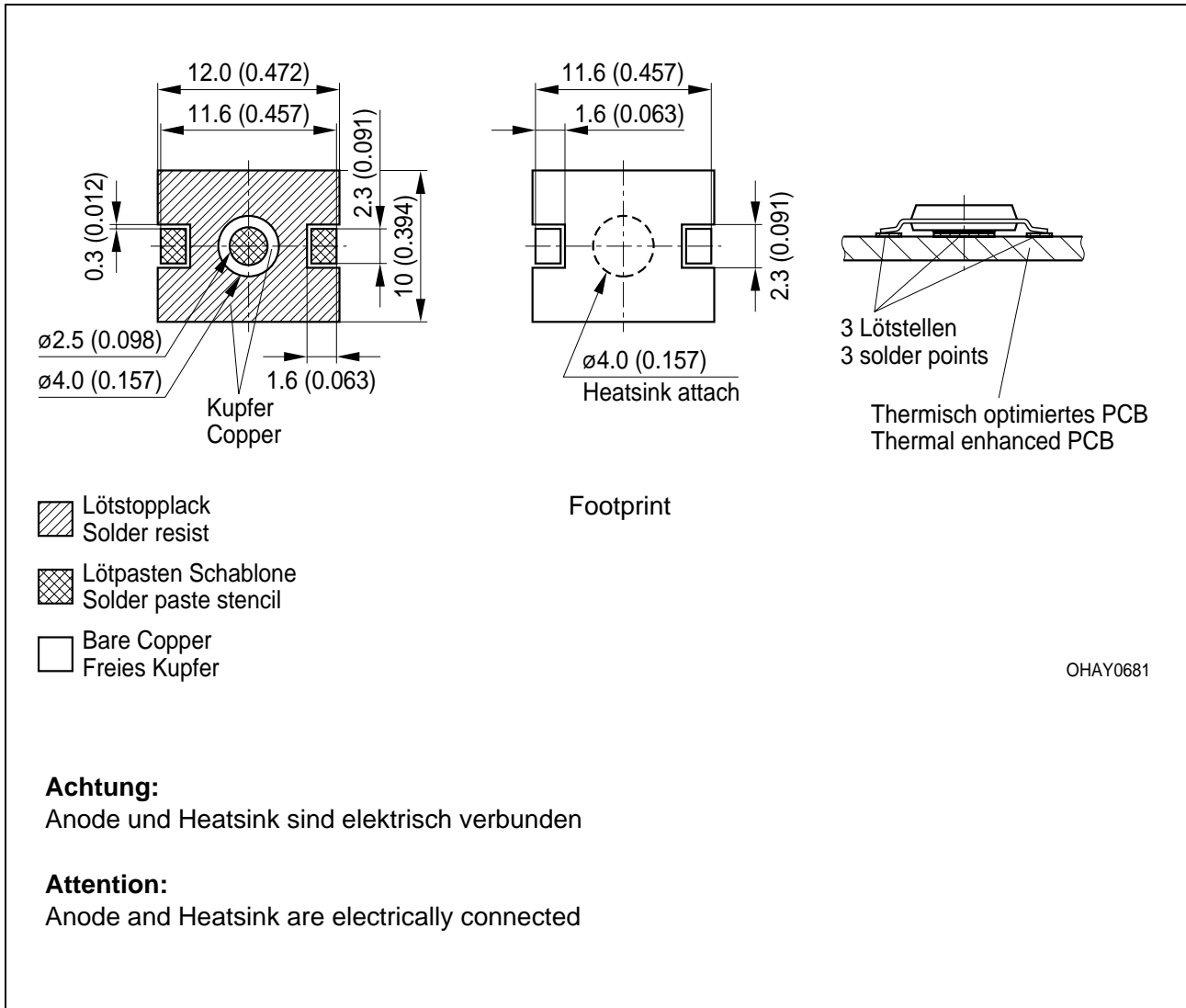
**Verpackungseinheit 800/Rolle, ∅180 mm**

**Packing unit 800/reel, ∅180 mm**



<sup>1)</sup> Maße in mm (inch) / Dimensions in mm (inch)

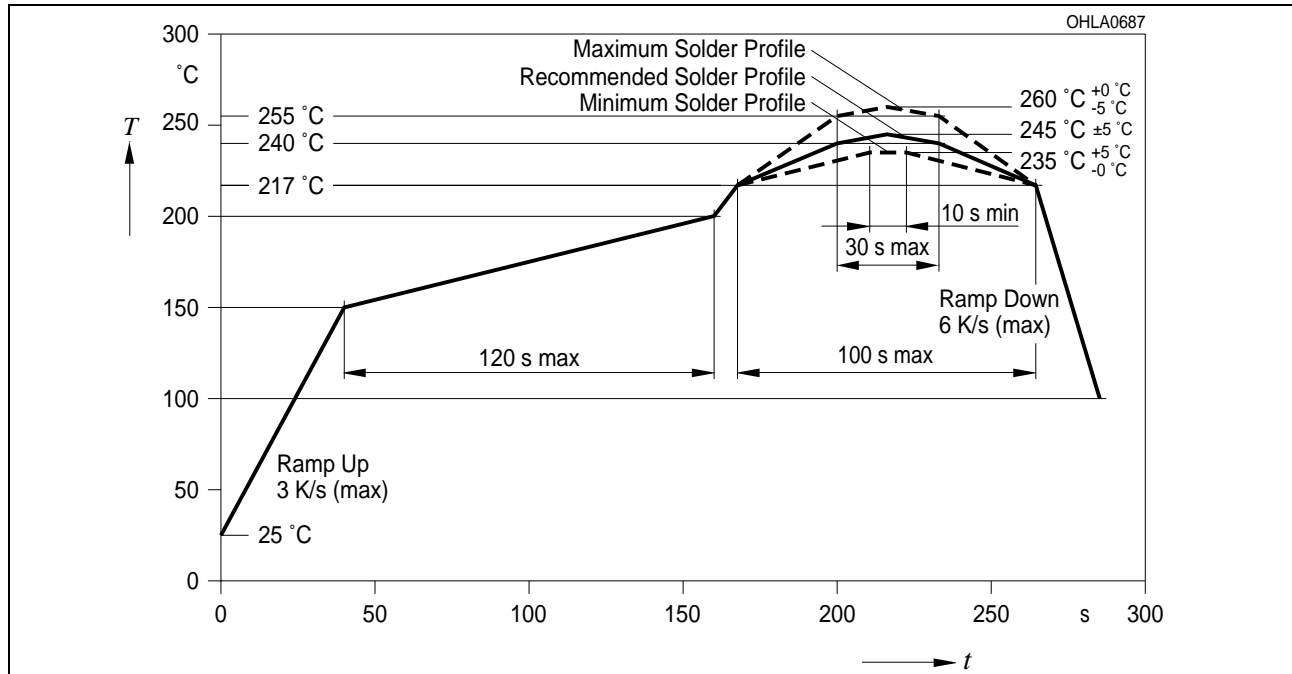
**Empfohlenes Lötpad Design**  
**Recommended Solder Pad Design**



**Lötbedingungen**  
**Soldering Conditions**

**Reflow Lötprofil für bleifreies Löten**  
**Reflow Soldering Profile for lead free soldering**

Vorbehandlung nach JEDEC Level 4  
Preconditioning acc. to JEDEC Level 4  
(nach J-STD-020C)  
(acc. to J-STD-020C)



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EU RoHS and China RoHS compliant product



此产品符合欧盟 RoHS 指令的要求；

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